华润微电子(重庆)有限公司

CRSG026N10N

SkyMOS1 N-MOSFET 100V, 2.3mΩ, 219A

Features

- Uses CRM(CQ) advanced SkyMOS1 technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent Q_gx$R_{DS(on)}$ product(FOM)
- Qualified according to JEDEC criteria

Product Summary

V_{DS}	100V
$R_{DS(on)}$	2.3mΩ
I_D	219A

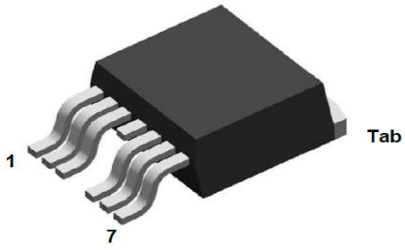
Applications

- Motor control and drive
- Battery management
- UPS (Uninterrupible Power Supplies)

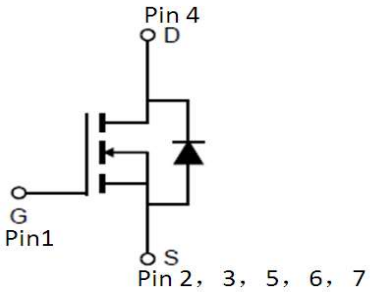
100% DVDS Tested

100% Avalanche Tested

RoHS HF



CRSG026N10N



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
CRSG026N10N	-	TO-263-6L	Tape	N/A	N/A	800pcs

Absolute Maximum Ratings

Parameter	**Symbol**	**Value**	**Unit**
Drain-source voltage	V_{DS}	100	V
Continuous drain current T_C = 25°C (Silicon limit) T_C = 25°C (Package limit) T_C = 100°C (Silicon limit)	I_D	 219 240 138	A
Pulsed drain current (T_C = 25°C, t_p limited by T_{jmax})	$I_{D\ pulse}$	876	A
Avalanche energy, single pulse (L=0.5mH, Rg=25Ω)[1]	E_{AS}	529	mJ
Gate-Source voltage	V_{GS}	±20	V
Power dissipation (T_C = 25°C)	P_{tot}	227	W
Operating junction and storage temperature	T_j , T_{stg}	-55...+150	°C

Notes:1.EAS was tested at Tj = 25℃, ID = 46A.

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Thermal Resistance

Parameter	Symbol	Max	Unit
Thermal resistance, junction – case.	R_{thJC}	0.55	°C/W
Thermal resistance, junction – ambient(min. footprint)	R_{thJA}	62	

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Static Characteristic						
Drain-source breakdown voltage	BV_{DSS}	100	-	-	V	V_{GS}=0V, I_D=250uA
Gate threshold voltage	$V_{GS(th)}$	2.2	3	3.8	V	V_{DS}=V_{GS},I_D=250uA
Zero gate voltage drain current	I_{DSS}	- -	0.05 -	1 100	μA	V_{DS}=100V,V_{GS}=0V T_j=25°C T_j=125°C
Gate-source leakage current	I_{GSS}	-	±10	±100	nA	V_{GS}=±20V,V_{DS}=0V
Drain-source on-state resistance	$R_{DS(on)}$	-	2.3	2.6	mΩ	V_{GS}=10V, I_D=90A
Transconductance	g_{fs}	-	197.2	-	S	V_{DS}=5V,I_D=100A
Dynamic Characteristic						
Input Capacitance	C_{iss}	-	11355	-	pF	V_{GS}=0V, V_{DS}=50V, f=1MHz
Output Capacitance	C_{oss}	-	1446	-		
Reverse Transfer Capacitance	C_{rss}	-	54	-		
Gate Total Charge	Q_G	-	169	-	nC	V_{GS}=10V, V_{DS}=50V, I_D=100A, f=1MHz
Gate-Source charge	Q_{gs}	-	67	-		
Gate-Drain charge	Q_{gd}	-	30	-		
Turn-on delay time	$t_{d(on)}$	-	35	-	ns	V_{GS}=10V, V_{DD}=50V, R_{G_ext}=3.0Ω
Rise time	t_r	-	111	-		
Turn-off delay time	$t_{d(off)}$	-	84	-		
Fall time	t_f	-	112	-		
Gate resistance	R_G	-	1.8	-	Ω	V_{GS}=0V, V_{DS}=0V, f=1MHz

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Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	0.9	1.4	V	V_{GS}=0V,I_{SD}=90A
Body Diode Reverse Recovery Time	t_{rr}	-	101	-	ns	I_F=100A, dI/dt=100A/μs
Body Diode Reverse Recovery Charge	Q_{rr}	-	338	-	nC	

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Typical Performance Characteristics

Fig 1: Output Characteristics

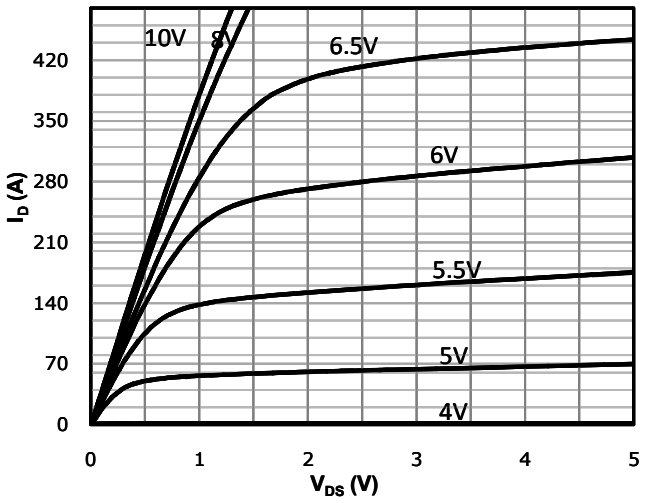
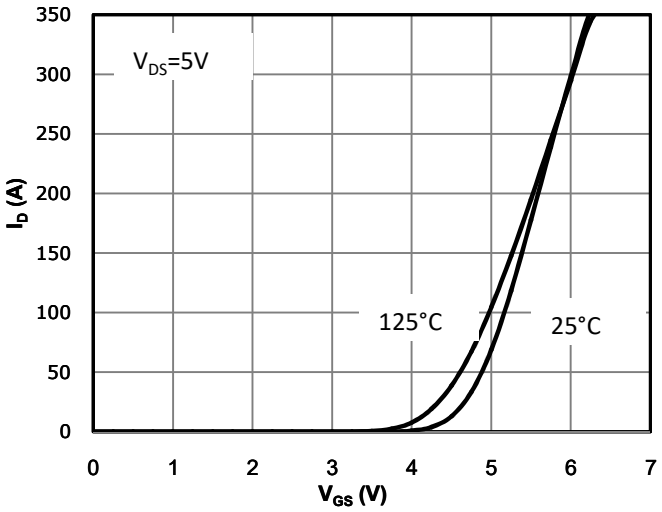


Fig 2: Transfer Characteristics



3: Rds(on) vs Drain Current and Gate Voltage

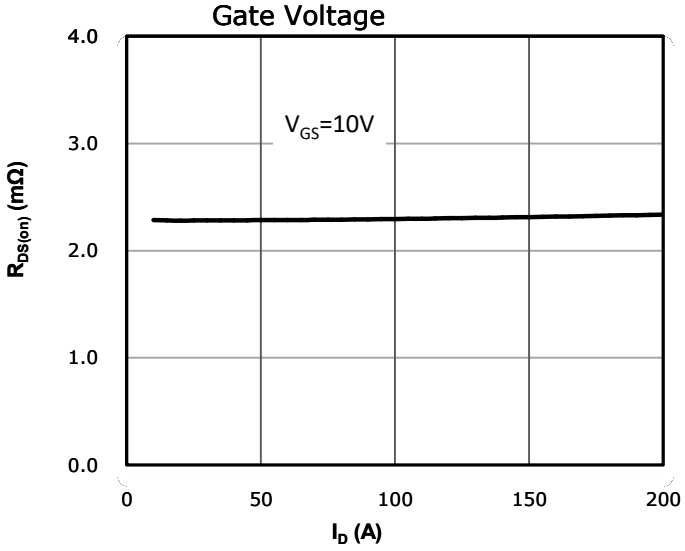


Fig 4: Rds(on) vs Gate Voltage

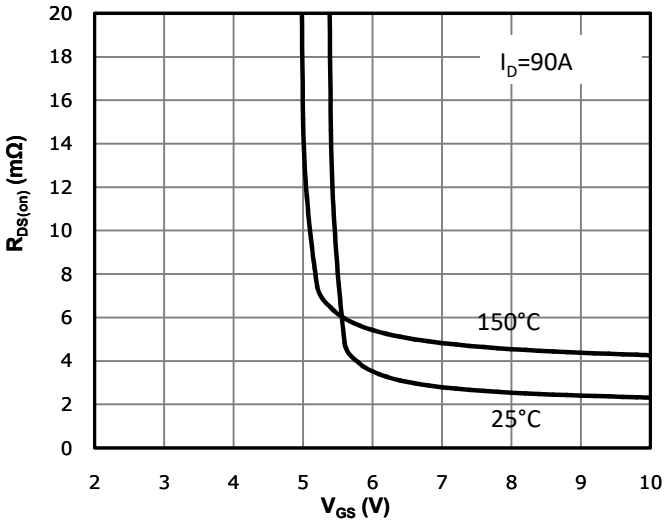


Fig 5: Rds(on) vs. Temperature

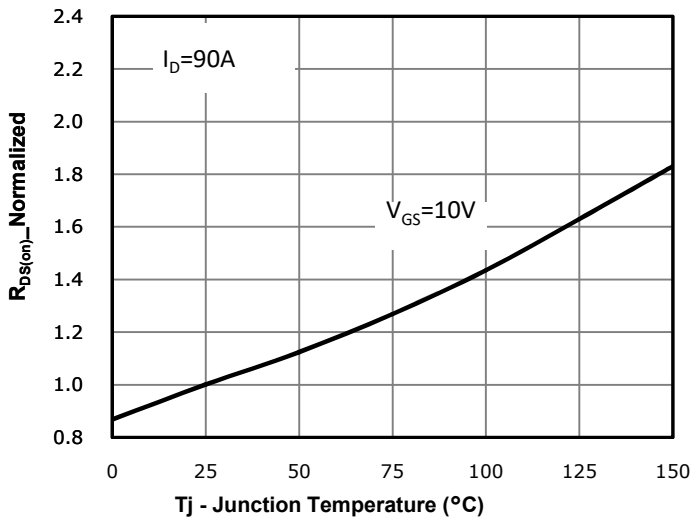
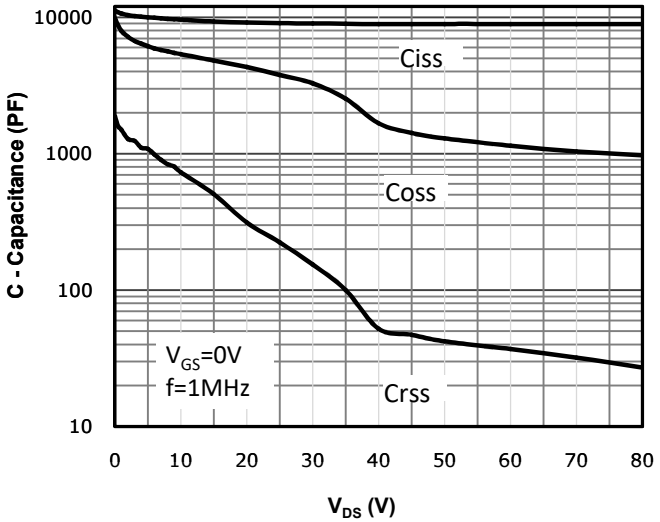


Fig 6: Capacitance Characteristics



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Fig 7: Gate Charge Characteristics

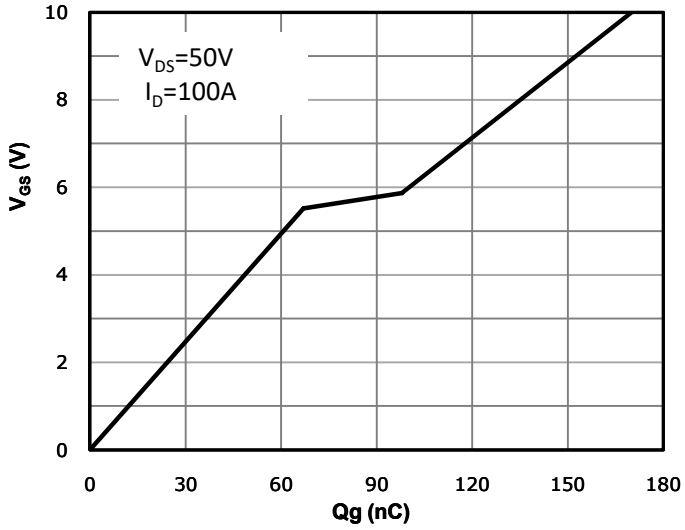


Fig 8: Body-diode Forward Characteristics

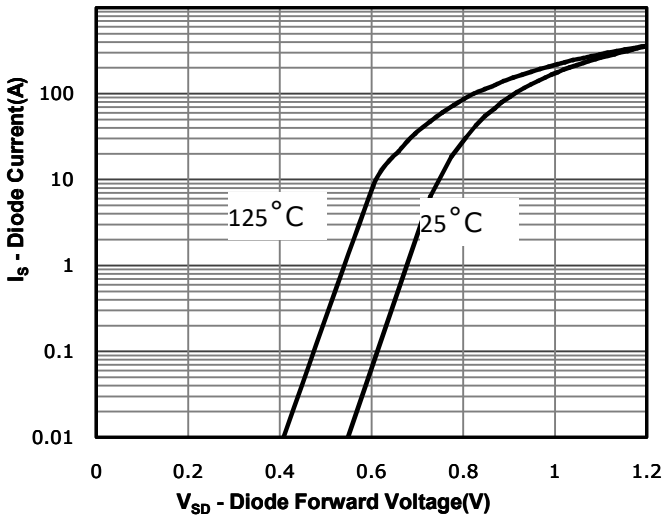


Fig 9: Power Dissipation

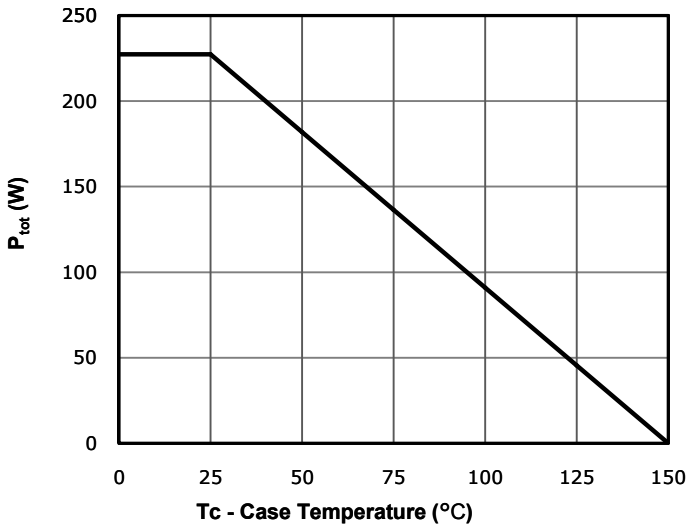


Fig 10: Drain Current Derating

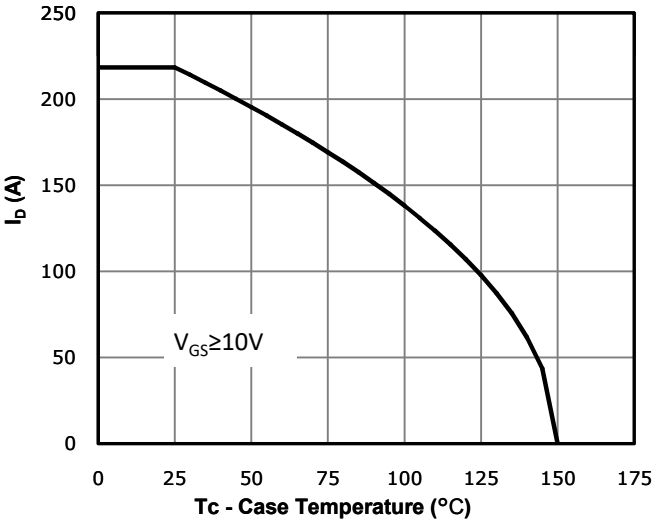
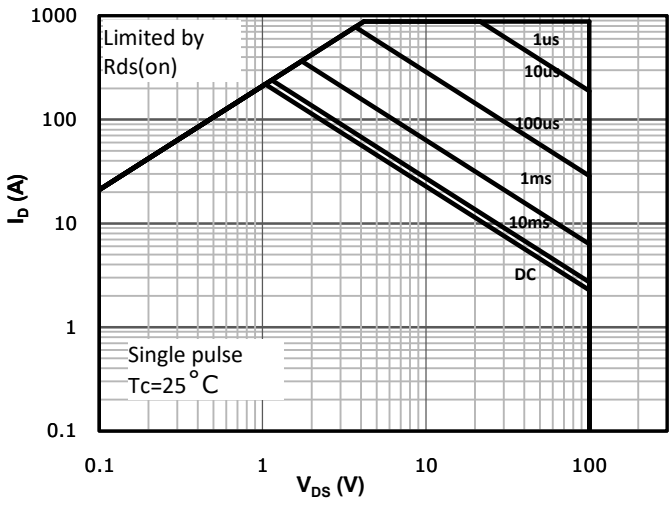
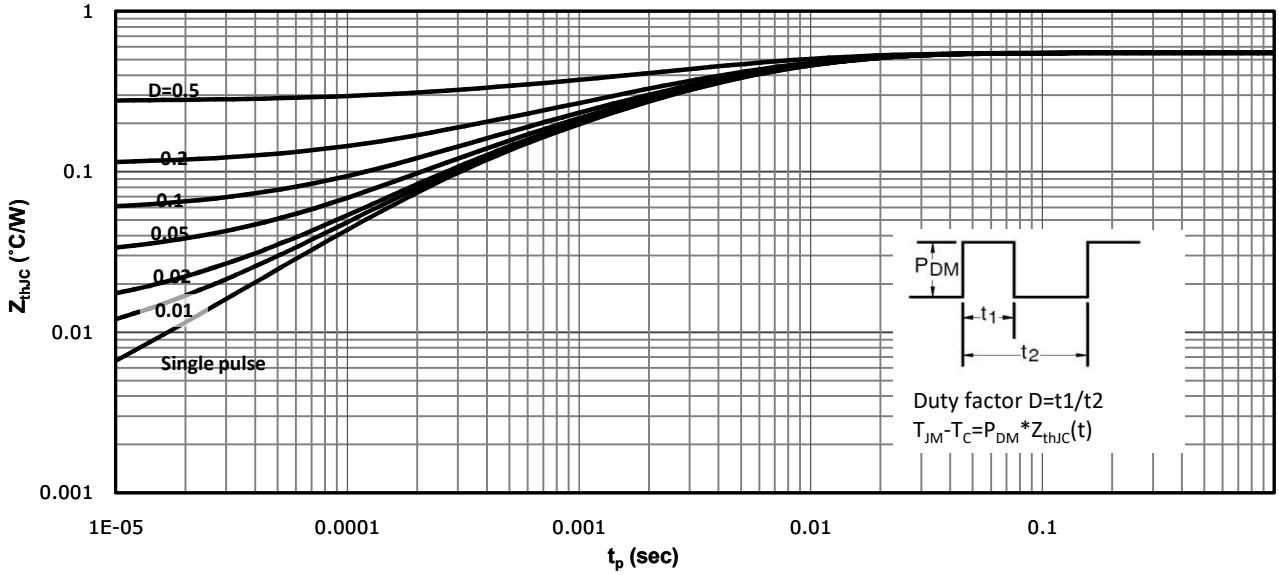


Fig 11: Safe Operating Area



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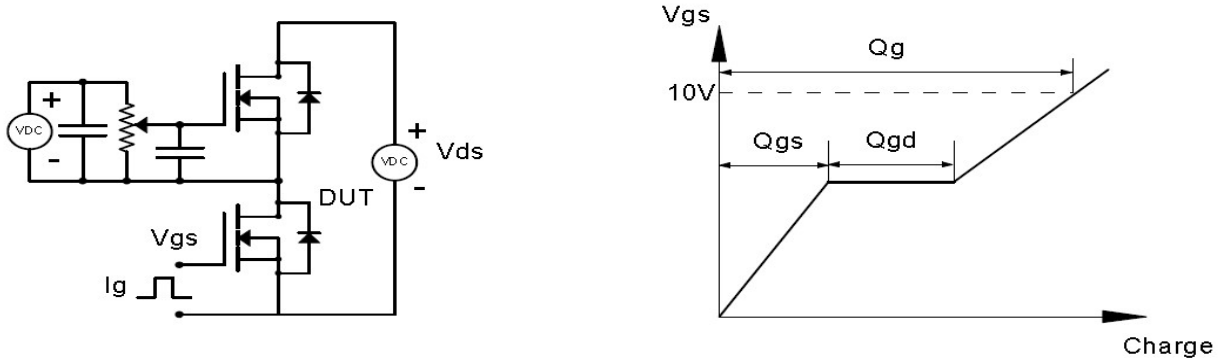
Fig 12: Max. Transient Thermal Impedance



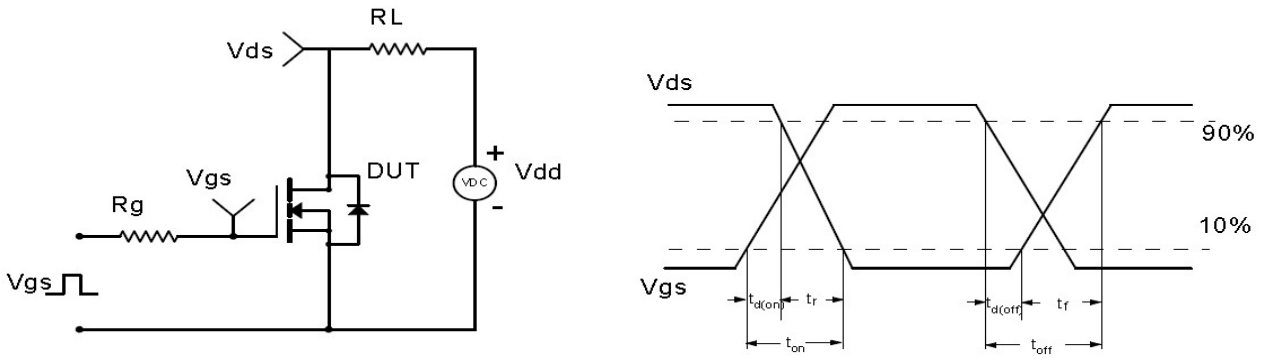
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Test Circuit & Waveform

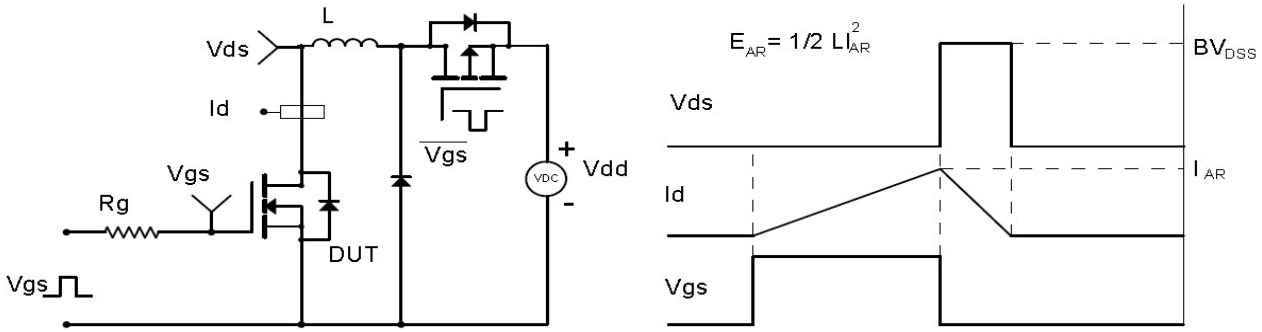
Gate Charge Test Circuit & Waveform



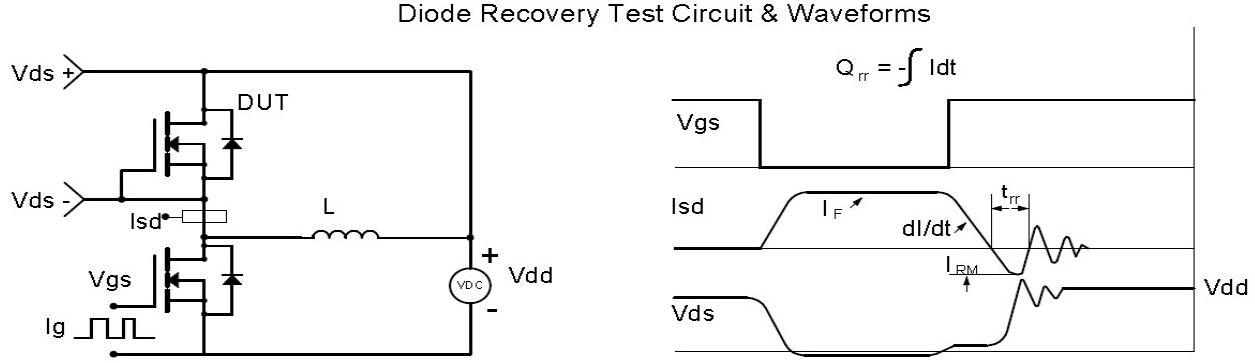
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

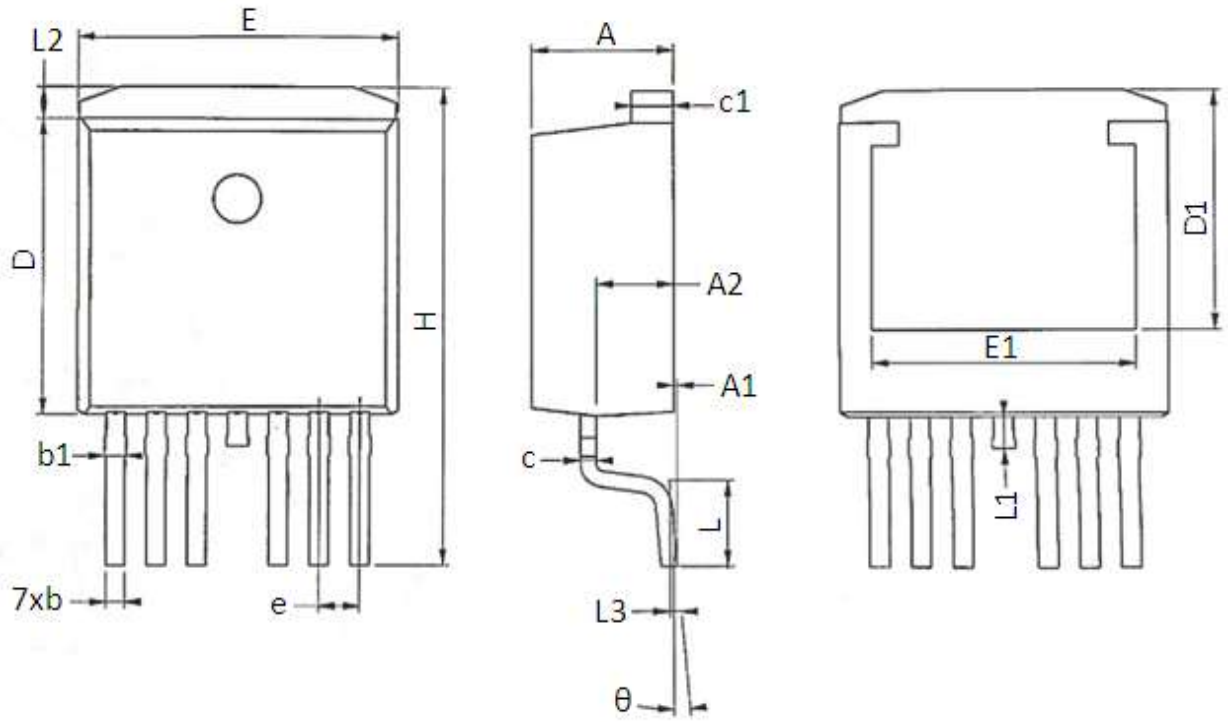


Diode Recovery Test Circuit & Waveforms



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Package Outline: TO-263-6L



Symbol		Dimensions In Millimeters		Dimensions In Inches	
		Min.	Max.	Min.	Max.
A		4.24	4.64	0.167	0.183
A1		0.00	0.25	0.000	0.010
A2		2.25	2.70	0.089	0.106
b		0.50	0.70	0.020	0.028
b1		0.50	0.90	0.020	0.035
c		0.40	0.60	0.016	0.024
c1		1.15	1.40	0.045	0.055
D		8.82	9.45	0.347	0.372
D1		6.80	--	0.268	--
e		1.27 BSC		0.050 BSC	
E		9.80	10.36	0.386	0.408
E1		7.25	--	0.285	--
H		14.61	15.88	0.575	0.625
L		1.78	3.00	0.070	0.118
L1		0.85	1.60	0.033	0.063
L2		0.80	1.60	0.031	0.063
L3		0.254 BSC		0.010 BSC	
θ	Option A	0°	8°	0°	8°
	Option B	0°	-8°	0°	-8°

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Revision History

Revison	Date	Major changes
1.0	2018-1-14	Release of formal version.
2.0	2019-6-25	Supplement package outline info.
2.1	2021-9-9	update Ron spec; update Ron & VSD test condition; package ordering & outline info.

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qulified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semicondutor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

CRM(CQ) reserves the right to improve product design, function and reliability without notice.

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